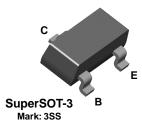


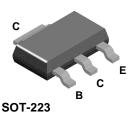
MPSA28

MMBTA28

PZTA28







NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from Process 03.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic		Units		
		MPSA28	*MMBTA28	**PZTA28	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

^{**}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

NPN Darlington Transistor

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Parameter Test Conditions				
055 0114	0.4.OTEDIOTIO0					
OFF CHAI	RACTERISTICS					
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu\text{A}, V_{BE} = 0$	80		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	80		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	12		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 60 \text{ V}, I_{E} = 0$		100	nA	
I _{CES}	Collector Cutoff Current	V _{CE} = 60 V, V _{BE} = 0		500	nA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA	

ON CHARACTERISTICS

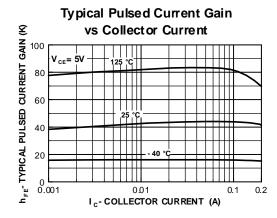
h _{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		
		$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$		1.2	V
(, , ,		$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$		1.5	
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$		2.0	V

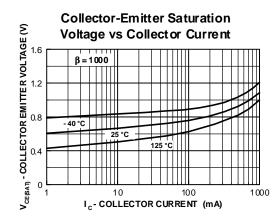
SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	125		MHz
C _{obo}	Output Capacitance	$V_{CB} = 1.0 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		8.0	pF

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics



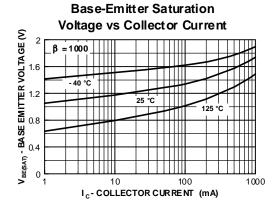


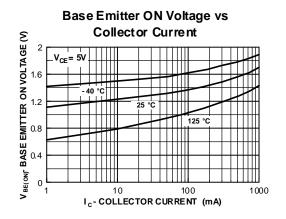
MPSA28/MMBTA28/PZTA28, Rev A

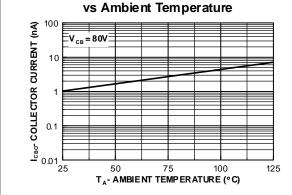
NPN Darlington Transistor

(continued)

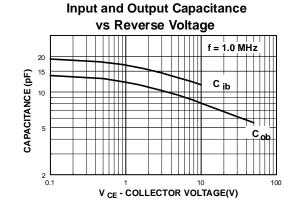
Typical Characteristics (continued)

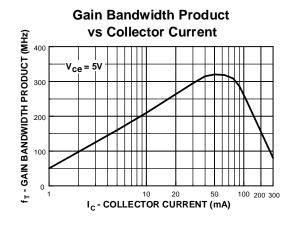


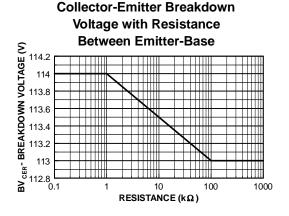




Collector-Cutoff Current





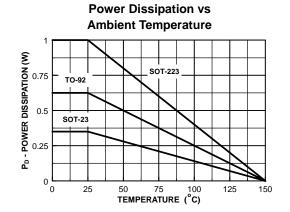


MPSA28/MMBTA28/PZTA28, Rev A

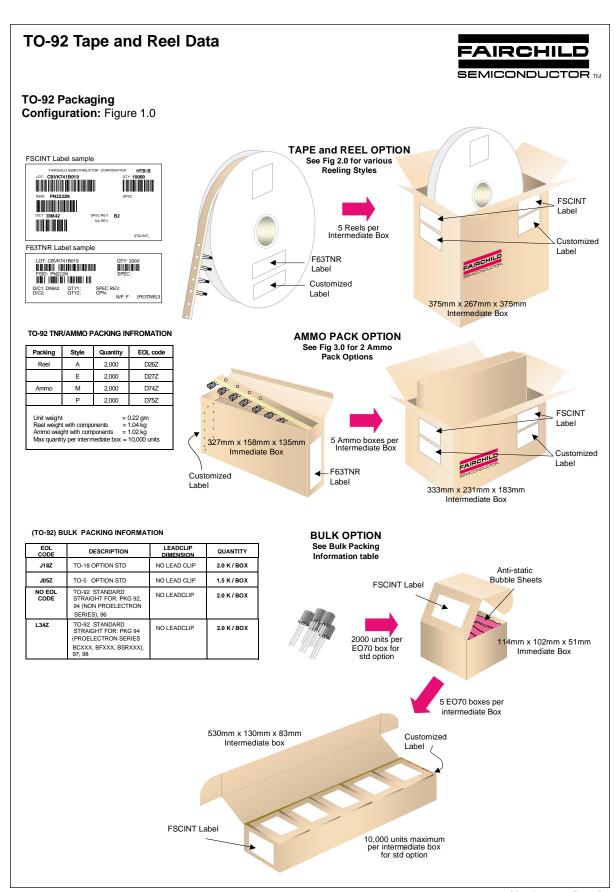
NPN Darlington Transistor

(continued)

Typical Characteristics (continued)



MPSA28/MMBTA28/PZTA28, Rev A

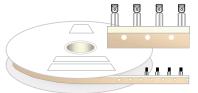


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



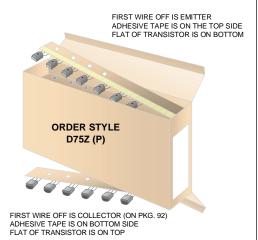
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

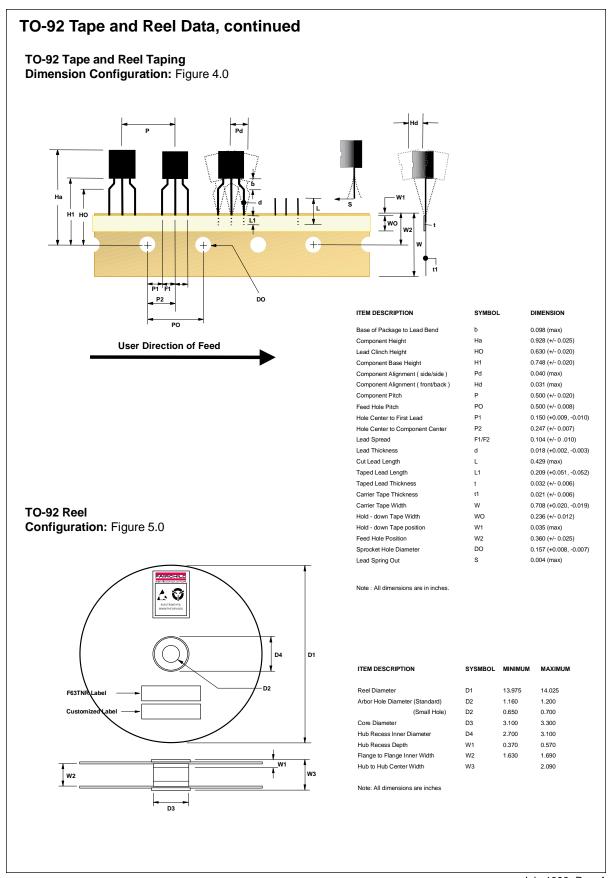
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B

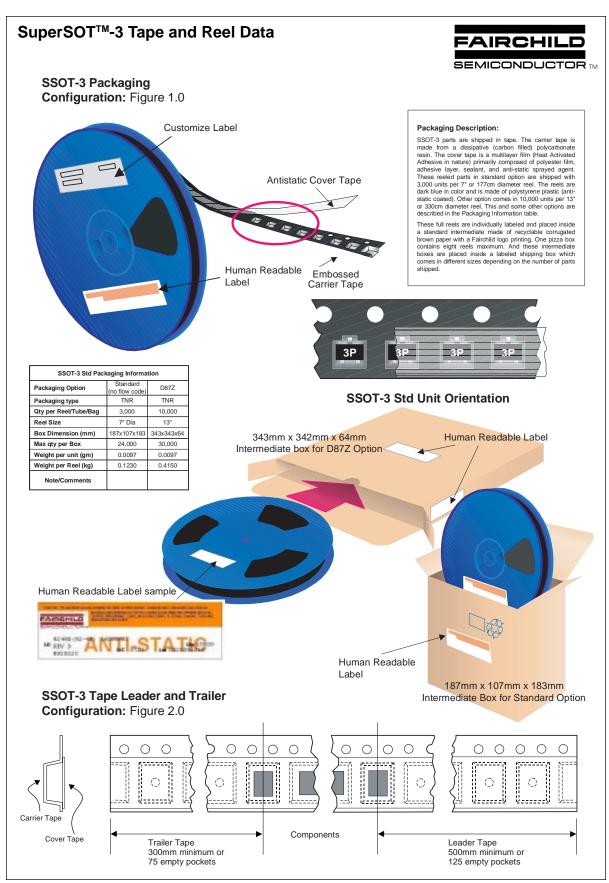


TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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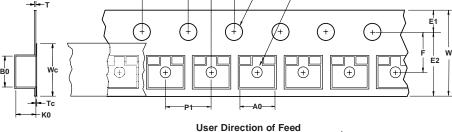
0.095 0.084 2.13

January 2000, Rev. B



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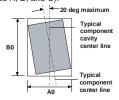


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

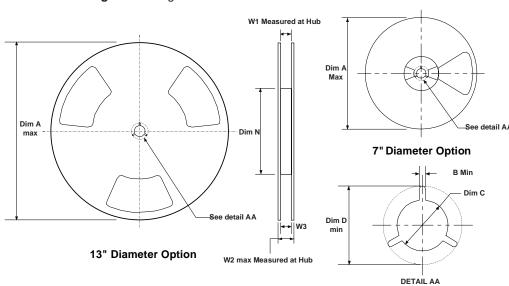


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SSOT-3 Reel Configuration: Figure 4.0

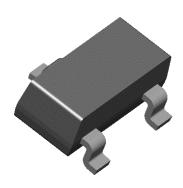


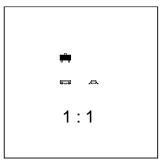
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

SuperSOT™-3 Package Dimensions



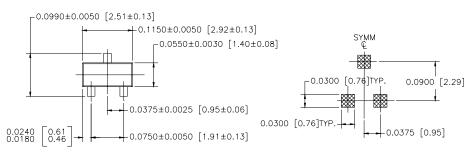
SuperSOT™-3 (FS PKG Code 32)



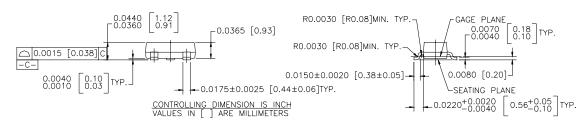


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



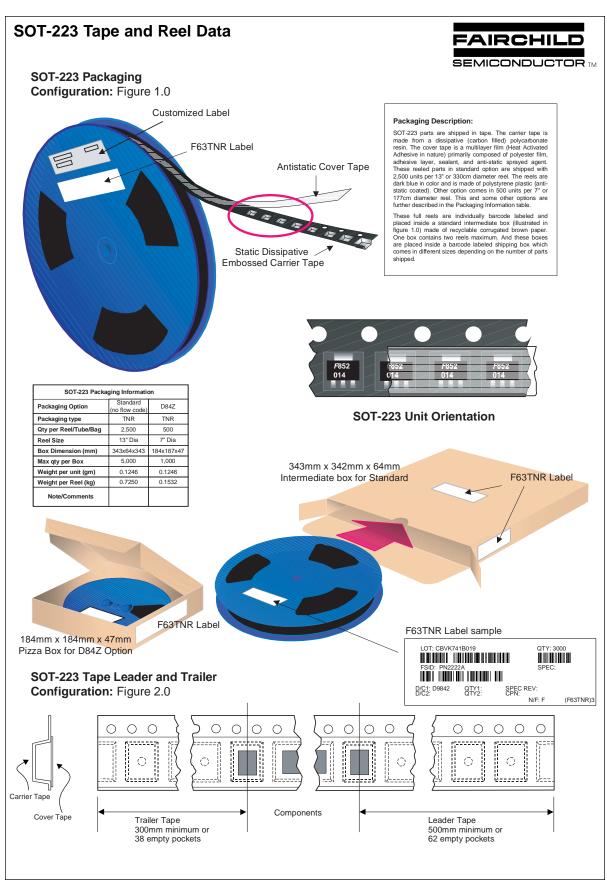
NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

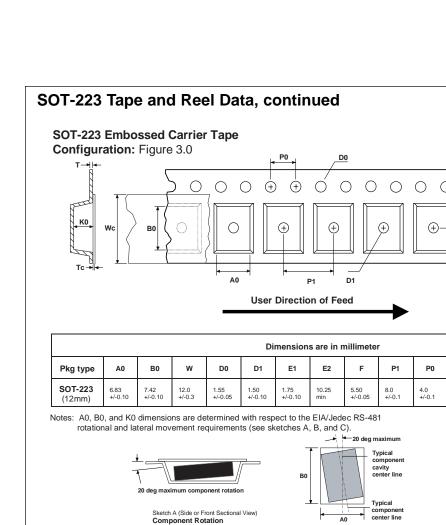
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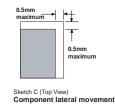
September 1998, Rev. A



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September 1999, Rev. B





0.292 +/-0.0130 Wc

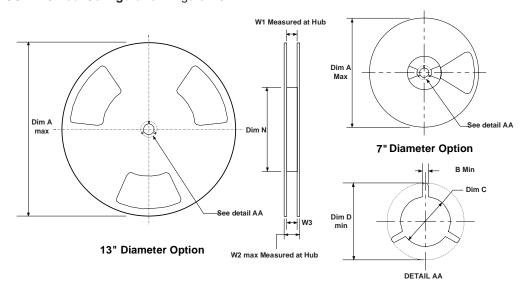
Tc

0.06 +/-0.02

K0

SOT-223 Reel Configuration: Figure 4.0





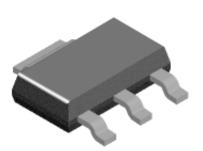
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	

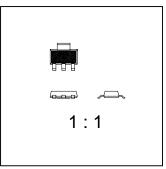
July 1999, Rev. B

SOT-223 Package Dimensions



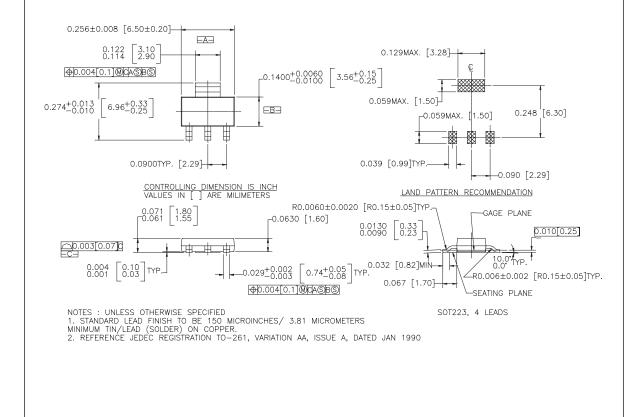
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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September 1999, Rev. C

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DOME™ ISOPLANAR™ Quiet Series™

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. G